

## **AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions and listings of claims in the application.

### **LISTING OF CLAIMS**

1. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a resin layer on a semiconductor substrate in which a plurality of integrated circuits are formed;

making a surface of the resin layer uneven by forming a plurality of recesses therein;

forming an interconnecting line on the resin layer, the interconnecting line contacting the surface of the resin layer with an interior of ~~ones~~ of the plurality of recesses along which the interconnecting line passes; and

cutting the semiconductor substrate into a plurality of semiconductor chips;

wherein each of the plurality of recesses is formed to have an opening width that is less than a thickness of the interconnecting line, and to have a depth of at least 1  $\mu\text{m}$ ,

the resin is formed of a photosensitive resin precursor,

photolithography using a mask is applied during the step of forming the plurality of recesses,

the mask includes a transparent-and-opaque pattern for irradiating the resin layer with a predetermined pattern that matches the transparent-and-opaque pattern,

the transparent-and-opaque pattern prevents the photosensitive resin precursor from being completely resolved by controlling an amount of energy applied to the resin layer during photolithography, and

the transparent-and-opaque pattern prevents the recesses from penetrating an entire thickness of the resin layer.

2. (Cancelled)

3. (Currently Amended) The method of manufacturing a semiconductor device as defined in claim [[2]] 1, wherein the photosensitive resin precursor is a negative type including an insoluble light-sensitive portion, and

wherein the transparent-and-opaque pattern includes an opaque portion having a width less than or equal to the thickness of the interconnecting line.

4. (Original) The method of manufacturing a semiconductor device as defined in claim 3, wherein the width of the opaque portion is less than or equal to one-fourths of a thickness of the resin layer.

5. (Original) The method of manufacturing a semiconductor device as defined in claim 1, further comprising:

roughening the surface of the resin layer including inner surfaces of the recesses, after forming the recesses and before forming the interconnecting line.

6. (Original) The method of manufacturing a semiconductor device as defined in claim 5, further comprising:

forming a second resin layer on the resin layer to cover at least a part of the interconnecting line, after forming the interconnecting line and before cutting the semiconductor substrate.

7. (Original) The method of manufacturing a semiconductor device as defined in claim 6, further comprising:

forming recesses and projections on a surface of the second resin layer.

8. (Original) The method of manufacturing a semiconductor device as defined in claim 7, further comprising:

forming a third resin layer on the second resin layer.

9. (Original) The method of manufacturing a semiconductor device as defined in claim 8, further comprising:

forming recesses and projections on a surface of the third resin layer.

10. – 31. (Cancelled)

32. (Previously Presented) The method of manufacturing a semiconductor device as defined in claim 1, wherein the recesses form an interconnected lattice in plan view.

33. (Previously Presented) The method of manufacturing a semiconductor device as defined in claim 1, wherein the recesses are disposed in an isolated manner in plan view.

34. (Previously Presented) The method of manufacturing a semiconductor device as defined in claim 1, wherein the recesses include a group of concentric ring-shaped recesses in plan view.